

<b>Notice of References Cited</b>			Application No. 09/116,138	Applicant(s) Anthony et al.		
			Examiner Bernard Sowu	Group Art Unit 2814		
<b>U.S. PATENT DOCUMENTS</b>						
	DOCUMENT NO.	DATE	NAME	CLASS		
A	5,834,353	11/10/98	Wu	438		
B	5,098,623	03/24/92	Pompe	264		
C	4,432,035	02/14/84	Hsieh et al.	361		
D	5,923,056	07/13/99	Lee et al.	257		
E	5,773,325	06/30/98	Teramoto	438		
F	5,874,766	02/23/99	Hori	257		
G	5,504,041	04/02/96	Summerfelt	438		
H	5,876,788	03/02/99	Bronner et al.	427		
I	5,851,896	12/22/98	Summerfelt	438		
J	5,187,636	02/16/93	Nakao	361		
K	5,173,835	12/22/92	Cornett et al.	257		
L	5,621,681	04/15/97	Moon	365		
M	5,528,068	06/18/96	Ohmi	257		
<b>FOREIGN PATENT DOCUMENTS</b>						
	DOCUMENT NO.	DATE	COUNTRY	NAME	CLASS	SUBCLASS
N	JP356073451	06/18/81	Japan	Iwai	H01L	21/88
O						
P						
Q						
R						
S						
T						
<b>NON-PATENT DOCUMENTS</b>						
	DOCUMENT (Including Author, Title, Source, and Pertinent Pages)				DATE	
u	Manchanda et al., "Gate quality doped high K films for CMOS beyond 100 nm: 3-10 nm Al <sub>2</sub> O <sub>3</sub> with low leakage and low interface states", IEEE Electron Devices Meeting, IEDM '98 Technical Digest, p.605-608				12/9/98	
v	Shimada et al., "Current drive enhancement by using high-permittivity gate insulator in SOI MOSFET's and its limitation", IEEE Trans. El. Devices, 43/3, 1996, pp. 431-435				3/96	
w	Shimada et al., "Minimum parasitic resistance for ultra-thin SOI MOSFET with high-permittivity gate insulator performed by lateral contact structure", Proc. 1995 IEEE International SOI Conference, pp. 98-99				10/5/95	
x	Chatterjee et al., "CMOS metal replacement gate transistors using tantalum pentoxide gate insulator", IEEE Electron Device Meeting, IEDM '98 Technical Digest, pp. 777-780				12/9/98	

<b>Notice of References Cited</b>			Application No. <b>09/116,138</b>	Applicant(s) <b>Anthony et al.</b>		
			Examiner <b>Bernard Souw</b>	Group Art Unit <b>2814</b>	<b>Page 2 of 3</b>	
<b>U.S. PATENT DOCUMENTS</b>						
	DOCUMENT NO.	DATE	NAME		CLASS	SUBCLASS
A	3,895,966	07/22/75	MacDougall et al.		317	235
B	5,880,006	03/09/99	Lin et al.		438	424
C	5,851,921	12/22/98	Gardner et al.		438	655
D	4,227,944	10/14/80	Brown et al.		148	6
E	4,952,992	08/28/90	Blanchard		357	23.4
F	5,053,917	10/01/91	Miyasaka et al.		361	321
G	5,686,748	11/11/97	Thakur et al.		257	310
H	5,227,320	07/13/93	Johnson et al.		438	304
I	5,182,232	01/26/93	Chhabra et al.		438	398
J	4,328,082	05/04/82	Neti et al.		204	195G
K	3,875,476	04/01/75	Crandall et al.		F23q 7	10
L	4,060,710	11/29/77	Reuter et al.		219	548
M	4,054,989	10/25/77	Ho et al.		29	571
<b>FOREIGN PATENT DOCUMENTS</b>						
	DOCUMENT NO.	DATE	COUNTRY	NAME	CLASS	SUBCLASS
N						
O						
P						
Q						
R						
S						
T						
<b>NON-PATENT DOCUMENTS</b>						
	DOCUMENT (Including Author, Title, Source, and Pertinent Pages)					DATE
u	Yongjoo et al., "Effect of barrier layer on the electrical and reliability characteristics of high-k gate dielectric films", IEEE Electron Devices Meeting, IEDM '98 Technical Digest, pp.797-800					12/9/98
v	Tseng et al., "Reduced gate leakage current and boron penetration of 0.18 um 1.5 V MOSFETs using integrated RTCVD Oxynitride gate dielectric", IEEE Electron Devices Meeting, IEDM '98 Technical Digest, pp.793-796					12/9/98
w	Liu, "Circuit requirement and integration challenges of thin gate dielectrics for ultra small MOSFETs", IEEE Electron Devices Meeting, IEDM '98 Technical Digest, pp.747-750					12/9/98
x						

<b>Notice of References Cited</b>		Application No. <b>09/116,138</b>	Applicant(s) <b>Anthony et al.</b>			
		Examiner <b>Bernard Souw</b>	Group Art Unit <b>2814</b>	Page 3 of 3		
<b>U.S. PATENT DOCUMENTS</b>						
	DOCUMENT NO.	DATE	NAME	CLASS	SUBCLASS	
A	5,665,966	09/09/97	Dahl et al.	250	281	
B						
C						
D						
E						
F						
G						
H						
I						
J						
K						
L						
M						
<b>FOREIGN PATENT DOCUMENTS</b>						
	DOCUMENT NO.	DATE	COUNTRY	NAME	CLASS	SUBCLASS
N						
O						
P						
Q						
R						
S						
T						
<b>NON-PATENT DOCUMENTS</b>						
	DOCUMENT (Including Author, Title, Source, and Pertinent Pages)				DATE	
U						
V						
W						
X						